

CLAIM SET AS AMENDED

Please amend the claims as follows:

1. (Previously Presented) A method of preventing generation of particles in a chamber, the method comprising:

mounting a substrate within a chamber of a gas-exposure equipment;

decreasing a pressure within the chamber;

injecting a surface treatment gas into the chamber, the surface treatment gas converting a surface of the substrate into an organic material;

increasing the pressure within the chamber to greater than or equal to atmospheric pressure by injecting a nitrogen gas into the chamber; and

drawing out the surface treatment gas from the chamber while injecting the nitrogen gas into the chamber and preventing atmospheric air and moisture from penetrating the chamber.

2-3. (Canceled)

4. (Currently Amended) The method as claimed in claim 1, wherein the surface treatment gas includes HMDS gas.

5. (Canceled)

6. (Original) The method as claimed in claim 1, wherein the chamber includes evacuation lines and ejection lines.

7. (Previously Presented) The method as claimed in claim 6, wherein the injecting nitrogen gas into the chamber includes injecting the nitrogen gas through the ejection lines.

8. (Currently Amended) The method as claimed in claim 6, wherein the step of evacuating includes evacuating the surface treatment gas through the evacuation lines.

9. (Original) The method as claimed in claim 1, wherein the substrate is a thin film transistor substrate.

10. (Original) The method as claimed in claim 9, wherein the thin film transistor substrate includes at least one of a gate electrode, a source electrode, a drain electrode, and a pixel electrode.

11. (Currently Amended) The method as claimed in claim 1, wherein the substrate includes a color filter substrate.

12. (Original) The method as claimed in claim 11, wherein the color filter substrate includes at least one of a color filter and a black matrix.

13. (Previously Presented) A method to prevent generation of contaminating particles in a chamber, the method comprising:

evacuating an ordinary gas within said chamber;

injecting a treatment gas into said chamber to treat a surface of a substrate;

increasing a pressure in said chamber to greater than or equal to atmospheric pressure by injecting a moisture displacing gas into the chamber; and

withdrawning said treatment gas from said chamber while injecting the moisture displacing gas into said chamber and preventing atmospheric air from entering the chamber.

14. (Original) The method of claim 13, wherein said moisture displacing gas is nitrogen.

15. (Original) The method of claim 13, wherein said treatment gas is HMDS.

16. (Canceled)